PROCESS CPD66X

Low Leakage Diode

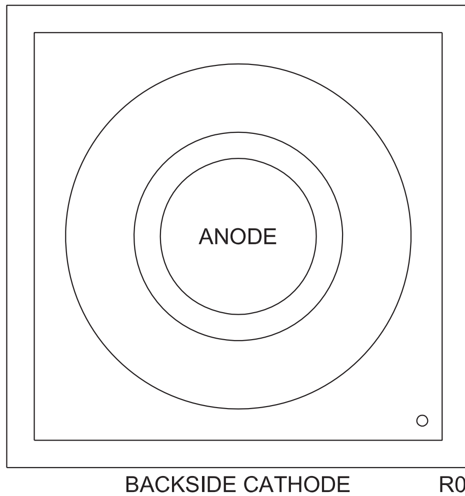
Low Leakage Diode Chip

www.DataSheet4U.com

PROCESS DETAILS

Die Size	17.5 x 17.5 MILS
Die Thickness	5.9 MILS
Anode Bonding Pad Area	7.9 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER

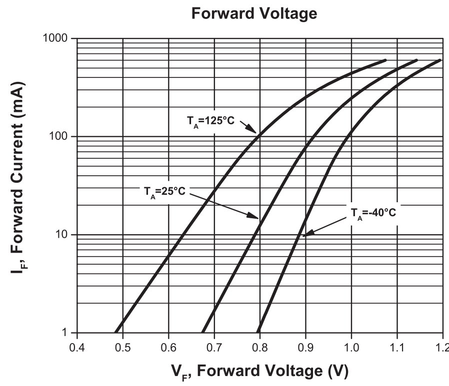
54,848

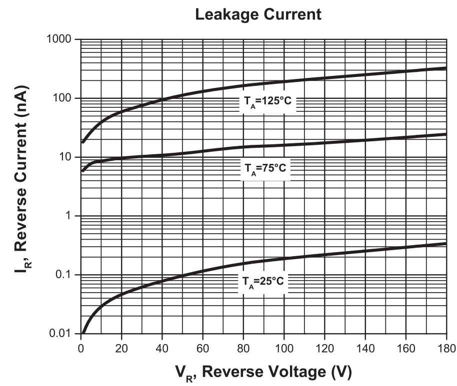
PRINCIPAL DEVICE TYPES

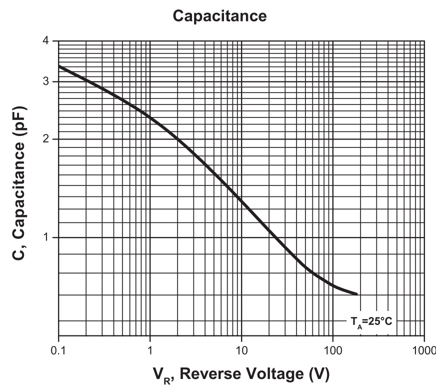
CMOD3003
CMLD3003DOG
CMPD3003A
CMPD3003C
CMPD3003S

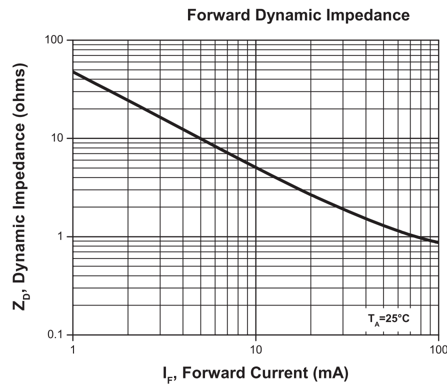
PROCESS CPD66X

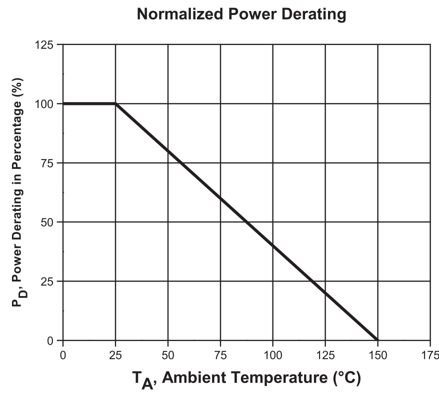
Typical Electrical Characteristics











R1 (19-July 2010)